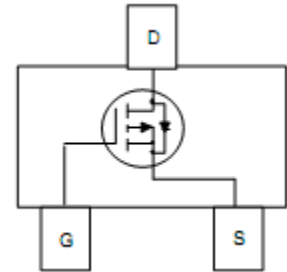


P-Channel Enhancement-Mode MOSFETs


SOT-23

■ MAXIMUM RATINGS

Characteristic	Symbol	Max	Unit
Drain-Source Voltage	BV_{DSS}	-30	V
Gate- Source Voltage	V_{GS}	± 12	V
Drain Current (continuous)	I_D	-2.6	A
Drain Current (pulsed)	I_{DM}	-18	A
Total Device Dissipation $T_A=25^\circ\text{C}$	P_D	1000	mW
Junction	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55to+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS

 (T_A=25°C unless otherwise noted 25°C)

Characteristic	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage (I _D = -250uA, V _{GS} =0V)	BV _{DSS}	-30	—	—	V
Gate Threshold Voltage (I _D = -250uA, V _{GS} = V _{DS})	V _{GS(th)}	-1.3	—	-2.3	V
Diode Forward Voltage Drop (I _S = -1A, V _{GS} =0V)	V _{SD}	—	—	-1	V
Zero Gate Voltage Drain Current (V _{GS} =0V, V _{DS} = -24V) (V _{GS} =0V, V _{DS} = -24V, T _A =55°C)	I _{DSS}	—	—	-1 -5	uA
Gate Body Leakage (V _{GS} =±12V, V _{DS} =0V)	I _{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance (I _D = -2.6A, V _{GS} = -10V)	R _{DS(ON)}	—	—	130	mΩ
Static Drain-Source On-State Resistance (I _D = -2A, V _{GS} = -4.5V)	R _{DS(ON)}	—	—	180	mΩ
Input Capacitance (V _{GS} =0V, V _{DS} = -15V, f=1MHz)	C _{ISS}	—	854	—	pF
Output Capacitance (V _{GS} =0V, V _{DS} = -15V, f=1MHz)	C _{OSS}	—	105	—	pF
Turn-ON Time (V _{DS} = -15V, V _{GS} = -10V, R _{GEN} =6Ω)	t _(on)	—	9	—	ns
Turn-OFF Time (V _{DS} = -15V, V _{GS} = -10V, R _{GEN} =6Ω)	t _(off)	—	38	—	ns

Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%